

NPN switching transistor

PZT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

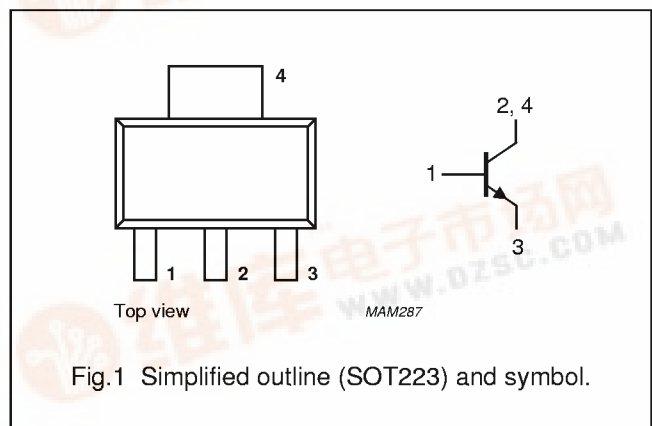
- Switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT223 plastic package.
PNP complement: PZT2907A.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	75	V
V_{CEO}	collector-emitter voltage	open base	—	40	V
V_{EBO}	emitter-base voltage	open collector	—	6	V
I_C	collector current (DC)		—	600	mA
I_{CM}	peak collector current		—	800	mA
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	1.15	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	109	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		28	K/W

Note

- Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

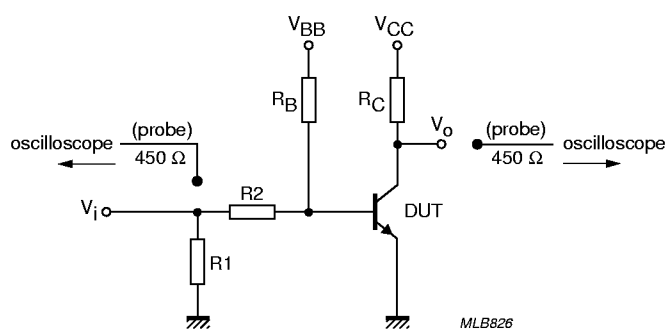
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 125\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	35	–	
		$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$	35	–	
		$I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$	50	–	
		$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	100	300	
		$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	300	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	0.6	1.2	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	2	V
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$I_C = I_E = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	25	pF
f_T	transition frequency	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	300	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}; T_{amb} = 25\text{ °C}$	–	35	ns
t_d	delay time		–	10	ns
t_r	rise time		–	25	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

- Pulse test: $t_p \leq 300\text{ μs}$; $\delta \leq 0.02$.

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$V_i = 9.5 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$.
 $R_1 = 68 \text{ } \Omega$; $R_2 = 325 \text{ } \Omega$; $R_B = 325 \text{ } \Omega$; $R_C = 160 \text{ } \Omega$.
 $V_{BB} = -3.5 \text{ V}$; $V_{CC} = 29.5 \text{ V}$.
Oscilloscope input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223

